

# Minghua Wang

## List of Publications by Year in descending order

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Version: 2024-02-01

13  
papers

373  
citations

1163117

8  
h-index

1199594

12  
g-index

13  
all docs

13  
docs citations

13  
times ranked

378  
citing authors

| #  | ARTICLE   | IF  | CITATIONS |
|----|---|-----|-----------|
| 1  | Localized surface plasmon resonance enhanced photoluminescence from SiNx with different N/Si ratios. Optical Materials Express, 2012, 2, 1437.  | 3.0 | 8         |
| 2  | Intense photoluminescence from Eu-doped silicon-rich silicon oxide films prepared by electron beam evaporation. , 2009, , .   |     | 0         |
| 3  | Enhanced photoluminescence of Tb <sup>3+</sup> in SnO <sub>2</sub> film by phosphorus diffusion process. Journal of Alloys and Compounds, 2009, 474, 246-249.                                     | 5.5 | 11        |
| 4  | Electron-beam-induced current evidence for room-temperature photoluminescence of silicon pn diode. Vacuum, 2008, 82, 1337-1340.   | 3.5 | 3         |
| 5  | Photoluminescence of Tb <sup>3+</sup> -doped SiNx films with different Si concentrations. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 126-130. | 3.5 | 6         |
| 6  | Electroluminescence of SnO <sub>2</sub> -p-Si heterojunction. Applied Physics Letters, 2008, 92, .  | 3.3 | 55        |
| 7  | Correlation between luminescence and structural evolution of Si-rich silicon oxide film annealed at different temperatures. Journal of Applied Physics, 2007, 101, 103504.                        | 2.5 | 29        |
| 8  | Photoluminescence of Si-rich silicon nitride: Defect-related states and silicon nanoclusters. Applied Physics Letters, 2007, 90, 131903.  | 3.3 | 124       |
| 9  | Effects of defect, carrier concentration and annealing process on the photoluminescence of silicon pn diodes. Materials Science in Semiconductor Processing, 2007, 10, 173-178.                   | 4.0 | 4         |
| 10 | Photoluminescence of Tb <sup>3+</sup> doped SiNx films grown by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2006, 100, 083106.   | 2.5 | 25        |
| 11 | An Iteration Method for the Computation of Potential and Current Distributions at a Partially Passivated Electrode. Journal of the Electrochemical Society, 1999, 146, 2853-2862.                 | 2.9 | 5         |
| 12 | Potential Distribution, Shape Evolution, and Modeling of Pit Growth for Ni in Sulfuric Acid. Journal of the Electrochemical Society, 1995, 142, 2986-2995.  | 2.9 | 43        |
| 13 | On Electric Field Induced Breakdown of Passive Films and the Mechanism of Pitting Corrosion. Journal of the Electrochemical Society, 1993, 140, 3448-3457.  | 2.9 | 60        |